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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>MB</i>	A191	2003/0080361 A1	05/01/2003	Murthy et al.			
<i>MB</i>	A192	5,821,577	10/13/1998	Crabbé et al.			
<i>MB</i>	A193	6,350,311 B1	02/26/2002	Chin et al.			
OTHER ART, JOURNAL ARTICLES, ETC.							
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)						
<i>MB</i>	C123	Examination Report for European Patent Application No. 98 931 529.6-2203, dated January 10, 2002, 4 pages.					
<i>MB</i>	C124	Examination Report for European Patent Application No. 98 931 529.6-2203, dated May 9, 2003, 5 pages.					
<i>MB</i>	C125	Examination Report for European Patent Application No. 01 973 651.1-1528, dated March 22, 2004, 3 pages.					
<i>MB</i>	C126	Examination Report for European Patent Application No. 01 989 893.1-1235, dated August 16, 2004, 5 pages.					
<i>MB</i>	C127	Examination Report for European Patent Application No. 01 973 651.1-1528, dated November 12, 2004, 9 pages.					
<i>MB</i>	C128	Examination Report for European Patent Application No. 02 709 406.9-2203, dated May 11, 2004, 3 pages.					
<i>MB</i>	C129	Examination Report for European Patent Application No. 02 709 406.9-2203, dated March 24, 2005, 5 pages.					
<i>MB</i>	C130	International Search Report for Patent Application No. PCT/US 98/13076, dated October 27, 1998, 2 pages.					
<i>MB</i>	C131	Notice of Preliminary Rejection for Korean Patent Application No. 10-1999-7012279, dated February 21, 2002, 2 pages (English translation attached).					
<i>MB</i>	C132	Notice of Final Rejection for Korean Patent Application No. 10-1999-7012279, dated February 25, 2003 2 pages (English translation attached).					
<i>MB</i>	C133	Klauck et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," Applied Physics Letter, No. 68, April 1, 1996, pgs. 1975-1977.					
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